



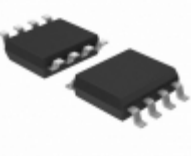

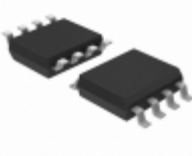
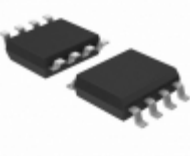

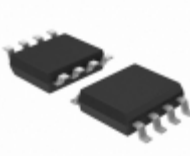

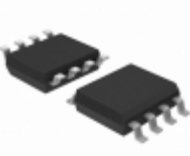
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|---|--|
|  | <p>SI4386DY-T1-GE3</p> |
| | <p>Hersteller-Teilenummer: SI4386DY-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 11A 8-SOIC</p> <p>Datenblätter:  SI4386DY-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 798200 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

| | |
|--|--|
| Teilenummer | SI4386DY-T1-GE3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET N-CH 30V 11A 8-SOIC |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 798200 pcs Stock |
| detaillierte Beschreibung | N-Channel 30V 11A (Ta) 1.47W (Ta) Surface Mount 8- |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | 8-SOIC (0.154", 3.90mm Width) |
| Supplier Device-Gehäuse | 8-SO |
| Verlustleistung (max) | 1.47W (Ta) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 30V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 11A (Ta) |
| Rds On (Max) @ Id, Vgs | 7 mOhm @ 16A, 10V |
| VGS (th) (Max) @ Id | 2.5V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 18nC @ 4.5V |
| Antriebsspannung (Max Rds On, Min Rds On) | 4.5V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Tape & Reel (TR) |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |
| Andere Namen | SI4386DY-T1-GE3TR |

SI4386DY-T1-GE3 ist neu im Original, Suche SI4386DY-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4386DY-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI4386DY-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|---|--|--|
|  <p>SI4386DY-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 11A 8-SOIC</p> |  <p>SI4388DY Vishay Precision Group SI4388DY VISHAY</p> |  <p>SI4388DY-T1-E3 Vishay / Siliconix MOSFET 2N-CH 30V 10.7A 8-SOIC</p> |  <p>SI4388DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 10.7A 8-SOIC</p> |
|  <p>SI4388DY-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 30V 10.7A 8-SOIC</p> |  <p>SI4386DY-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 11A 8-SOIC</p> |  <p>SI4386DY-T1-E3.. VISHAY SI4386DY-T1-E3.. VISHAY</p> |  <p>SI4386DY-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 11A 8-SOIC</p> |

heiße Teile

Mehr

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|---------------------|------------------|-----------------|-----------------|------------------|
| SI4362BDY-T1-E3-PBF | SI4362DY | SI4362DY-T1 | SI4362DY-T1-E3 | SI4362DY-T1-E3. |
| SI4364DY | SI4364DY-T1 | SI4364DY-T1-E3 | SI4366DY-T1-E3 | SI4368DY |
| SI4368DY-T1-E3 | SI4368DY-T1-E3 | SI4370DY-T1-E3 | SI4376DY-T1-E3 | SI4378DY-T1 |
| SI4378DY-T1-E3 | SI4378DY-T1-E3 | SI4382DY-T1-E3 | SI4384DY | SI4384DY-T1-E3 |
| SI4384DY-T1-E3 | SI4384DY-T1-E3.. | SI4386DY | SI4386DY-T1-E3 | SI4386DY-T1-E3 |
| SI4386DY-T1-GE3 | SI4388DY | SI4388DY-T1-GE3 | SI4388DY-T1-GE3 | SI4390DY |
| SI4390DY-T1 | SI4390DY-T1-E3 | SI4390DY-T1-E3 | SI4390DY-T1-E3 | SI4392ADY |
| SI4392ADY-T1-E3 | SI4392DY | SI4392DY-T1-E3 | SI4392DY-T1-E3. | SI4392DY-T1-E3.. |
| SI4394DY | SI4394DY-T1-E3 | SI4396DY | SI4396DY-T1-E3 | SI4396DY-T1-E3 |
| SI4398DY-T1-E3 | SI4398DY-T1-E3 | SI4401BDY-T1-E3 | SI4401BDY-T1-E3 | SI4401BDY-T1-E3. |

Contact us: Info@Y-IC.com

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